

# 2STA1962

# High power PNP epitaxial planar bipolar transistor

## Features

- High breakdown voltage V<sub>CEO</sub> = -230 V
- Complementary to 2STC5242
- Fast-switching speed
- Typical f<sub>T</sub> = 30 MHz

# Application

Audio power amplifier

# Description

This device is a PNP transistor manufactured using new BiT-LA (Bipolar Transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

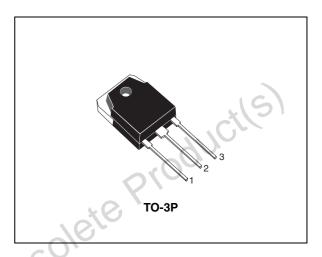


Figure 1. Internal schematic diagram

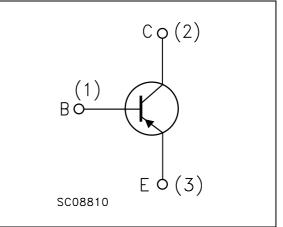


Table 1.	Device	summary
	Device	Sammary

Order code	Marking	Package	Packaging
2STA1962	2STA1962	TO-3P	Tube

July 2	800
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#### **Electrical ratings** 1

Table 2.	Absolute	maximum	ratings
	Absolute	IIIUAIIIIUIII	ruungo

V <sub>CBO</sub> V <sub>CEO</sub>	Collector-base voltage ( $I_E = 0$ )		
V <sub>CEO</sub>		-230	V
	Collector-emitter voltage (I <sub>B</sub> = 0)	-230	V
$V_{EBO}$	Emitter-base voltage ( $I_{\rm C} = 0$ )	-5	V
Ι <sub>C</sub>	Collector current	-15	А
I <sub>CM</sub>	Collector peak current	-30	А
P <sub>tot</sub>	Total dissipation at $T_{C} = 25 \ ^{\circ}C$	150	W
T <sub>stg</sub>	Storage temperature	-55 to 150	°C
Т <sub>Ј</sub>	Operating junction temperature	150	°C
		01	
able 3.	Thermal data	×C `	

#### Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thJ-case</sub>	Thermal resistance junction-case Max	0.83	°C/W
	005		
	<b>O</b>		
	4(5)		
	00		
0	$\langle O \rangle$		
. 0. 1	oducils		
Clo			



# 2 Electrical characteristics

(T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> = 0)	V <sub>CB</sub> = -230 V			-5	μΑ
I <sub>EBO</sub>	Emitter cut-off current $(I_{C} = 0)$	V <sub>EB</sub> = -5 V			-5	μA
V <sub>(BR)CEO</sub> <sup>(1)</sup>	Collector-emitter breakdown voltage ( $I_B = 0$ )	I <sub>C</sub> = -50 mA	-230			v
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = -100 μA	-230	30		v
V <sub>(BR)EBO</sub> <sup>(1)</sup>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = -1 mA	-5			v
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	I <sub>C</sub> = -8 A I <sub>B</sub> = -800 mA			-3	v
$V_{BE}$	Base-emitter voltage	$I_{C} = -7 A$ $V_{CE} = -5 V$			-1.5	v
h <sub>FE</sub>	DC current gain	$I_{C} = -1 A$ $V_{CE} = -5 V$ $I_{C} = -7 A$ $V_{CE} = -5 V$	80 35		160	
t <sub>on</sub> t <sub>s</sub> t <sub>f</sub>	Resistive load Turn-on time Storage time Fall time	$V_{CC} = -60 V I_{C} = -5 A$ $I_{B1} = -I_{B2} = -0.5 A$		0.24 1.2 0.21		μs μs μs
f <sub>T</sub>	Transition frequency	$I_{C} = -1 A$ $V_{CE} = -5 V$		30		MHz
C <sub>CBO</sub>	Collector-base capacitance $(I_E = 0)$	V <sub>CB</sub> = -10 V f = 1 MHz		150		pF

Table 4. Electrical characteristics	Table 4.	Electrical characteristics
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1. Pulsed: pulse duration = 300  $\mu s,$  duty cycle  $\leq 1.5\%$ 

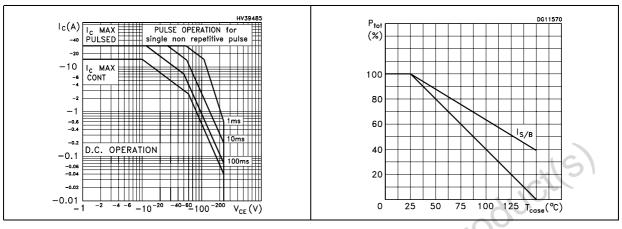
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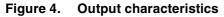
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### 2.1 Electrical characteristics (curves)

#### Figure 2. Safe operating area

Figure 3. Derating curve







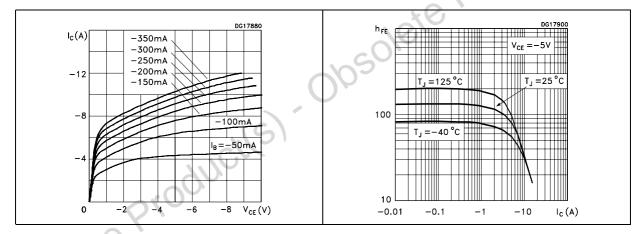
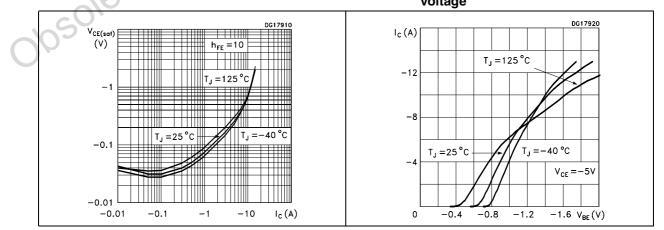
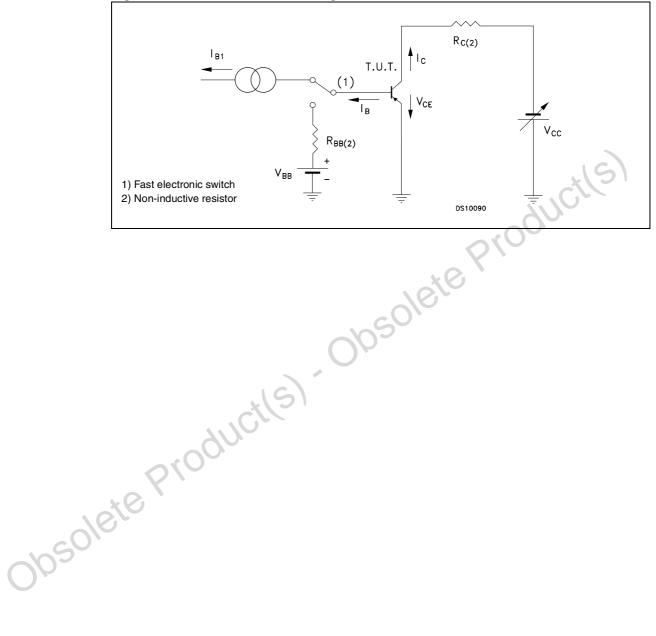


Figure 6. Collector-emitter saturation voltage Figure 7. Collector current vs base-emitter voltage



## 2.2 Test circuit



### Figure 8. Resistive load switching test circuit



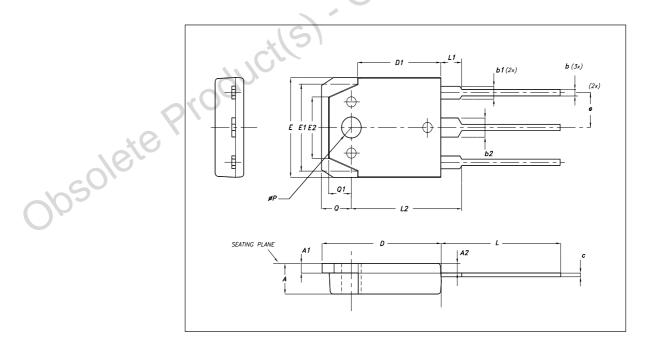
# 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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TO-3P Mechanical data				
DIM.		mm.		
	MIN.	ТҮР	MAX.	
A	4.6		5	
A1	1.45	1.50	1.65	
A2	1.20	1.40	1.60	
b	0.80	1	1.20	
b1	1.80		2.20	
b2	2.80		3.20	
С	0.55	0.60	0.75	
D	19.70	19.90	20.10	
D1		13.90	AU.	
E	15.40		15.80	
E1		13.60		
E2		9.60		
е	5.15	5.45	5.75	
L	19.50	20	20.50	
L1		3.50		
L2	18.20	18.40	18.60	
P	3.10	<u> </u>	3.30	
Q		5		
Q1		3.80		



# 4 Revision history

#### Table 5.Document revision history

	Date	Revision	Changes
	28-Sep-2007	1	Initial release.
	12-Dec-2007	2	Document promoted from preliminary data to datasheet.
	15-Jul-2008	3	Updated total power dissipation and relevant thermal resistance junction-case value.
obsole	eprod	Jucils	junction-case value.



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